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## Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	768
Total RAM Bits	-
Number of I/O	77
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agln030v5-zvqg100i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



## User Nonvolatile FlashROM

IGLOO nano devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- · Internet protocol addressing (wireless or fixed)
- · System calibration settings
- Device serialization and/or inventory control
- · Subscription-based business models (for example, set-top boxes)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard IGLOO nano IEEE 1532 JTAG programming interface. The core can be individually programmed (erased and written), and on-chip AES decryption can be used selectively to securely load data over public networks (except in the AGLN030 and smaller devices), as in security keys stored in the FlashROM for a user design.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

The IGLOO nano development software solutions, Libero<sup>®</sup> System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature enables the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Microsemi Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.

### SRAM and FIFO

IGLOO nano devices (except the AGLN030 and smaller devices) have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro (except in the AGLN030 and smaller devices).

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

### PLL and CCC

Higher density IGLOO nano devices using either the two I/O bank or four I/O bank architectures provide designers with very flexible clock conditioning capabilities. AGLN060, AGLN125, and AGLN250 contain six CCCs. One CCC (center west side) has a PLL. The AGLN030 and smaller devices use different CCCs in their architecture (CCC-GL). These CCC-GLs contain a global MUX but do not have any PLLs or programmable delays.

For devices using the six CCC block architecture, these are located at the four corners and the centers of the east and west sides. All six CCC blocks are usable; the four corner CCCs and the east CCC allow simple clock delay operations as well as clock spine access.

### Combinatorial Cells Contribution—P<sub>C-CELL</sub>

 $P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * PAC7 * F_{CLK}$ 

N<sub>C-CFLL</sub> is the number of VersaTiles used as combinatorial modules in the design.

 $\alpha_{\text{1}}$  is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-14.

F<sub>CLK</sub> is the global clock signal frequency.

## Routing Net Contribution—P<sub>NET</sub>

 $P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * PAC8 * F_{CLK}$ 

N<sub>S-CELL</sub> is the number of VersaTiles used as sequential modules in the design.

N<sub>C-CFLL</sub> is the number of VersaTiles used as combinatorial modules in the design.

 $\alpha_1$  is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-19 on page 2-14.

F<sub>CLK</sub> is the global clock signal frequency.

### I/O Input Buffer Contribution—PINPUTS

 $P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * PAC9 * F_{CLK}$ 

N<sub>INPLITS</sub> is the number of I/O input buffers used in the design.

 $\alpha_2$  is the I/O buffer toggle rate—guidelines are provided in Table 2-19 on page 2-14.

F<sub>CLK</sub> is the global clock signal frequency.

### I/O Output Buffer Contribution—POUTPUTS

 $P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * PAC10 * F_{CLK}$ 

 $N_{\mbox{OUTPUTS}}$  is the number of I/O output buffers used in the design.

 $\alpha_2$  is the I/O buffer toggle rate—guidelines are provided in Table 2-19 on page 2-14.

 $\beta_1$  is the I/O buffer enable rate—guidelines are provided in Table 2-20 on page 2-14.

F<sub>CLK</sub> is the global clock signal frequency.

### RAM Contribution—P<sub>MEMORY</sub>

 $\mathsf{P}_{\mathsf{MEMORY}} = \mathsf{PAC11} * \mathsf{N}_{\mathsf{BLOCKS}} * \mathsf{F}_{\mathsf{READ\text{-}CLOCK}} * \beta_2 + \mathsf{PAC12} * \mathsf{N}_{\mathsf{BLOCK}} * \mathsf{F}_{\mathsf{WRITE\text{-}CLOCK}} * \beta_3$ 

N<sub>BLOCKS</sub> is the number of RAM blocks used in the design.

F<sub>READ-CLOCK</sub> is the memory read clock frequency.

 $\beta_2$  is the RAM enable rate for read operations.

F<sub>WRITE-CLOCK</sub> is the memory write clock frequency.

 $\beta_3$  is the RAM enable rate for write operations—guidelines are provided in Table 2-20 on page 2-14.

### PLL Contribution—P<sub>PLL</sub>

P<sub>PLL</sub> = PDC4 + PAC13 \*F<sub>CLKOUT</sub>

F<sub>CLKOUT</sub> is the output clock frequency.<sup>1</sup>

If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution (PAC13\* FCLKOUT product) to the total PLL contribution.



### Applies to IGLOO nano at 1.5 V Core Operating Conditions

Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings STD Speed Grade, Commercial-Case Conditions:  $T_J = 70^{\circ}\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

I/O Standard	Drive Strength (mA)	Equivalent Software Default t Drive Strength Option <sup>1</sup>	Slew Rate	Capacitive Load (pF)	tвоит	top	<sup>‡</sup> DIN	tрү	tpys	t <sub>EOUT</sub>	<sup>t</sup> zı.	tz <del>1</del>	t <sub>LZ</sub>	t <sub>НZ</sub>	Units
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	5 pF	0.97	1.79	0.19	0.86	1.16	0.66	1.83	1.45	1.98	2.38	ns
3.3 V LVCMOS Wide Range <sup>2</sup>	100 μΑ	8 mA	High	5 pF	0.97	2.56	0.19	1.20	1.66	0.66	2.57	2.02	2.82	3.31	ns
2.5 V LVCMOS	8 mA	8 mA	High	5 pF	0.97	1.81	0.19	1.10	1.24	0.66	1.85	1.63	1.97	2.26	ns
1.8 V LVCMOS	4 mA	4 mA	High	5 pF	0.97	2.08	0.19	1.03	1.44	0.66	2.12	1.95	1.99	2.19	ns
1.5 V LVCMOS	2 mA	2 mA	High	5 pF	0.97	2.39	0.19	1.19	1.52	0.66	2.44	2.24	2.02	2.15	ns

#### Notes:

- The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
- 2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification.
- 3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

## Input Register

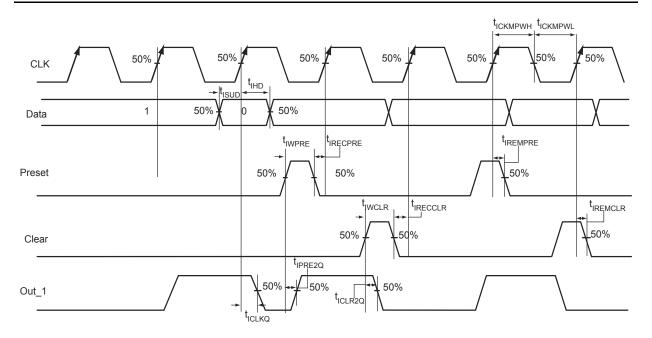


Figure 2-14 • Input Register Timing Diagram

### **Timing Characteristics**

1.5 V DC Core Voltage

Table 2-72 • Input Data Register Propagation Delays
Commercial-Case Conditions: T<sub>J</sub> = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t <sub>ICLKQ</sub>	Clock-to-Q of the Input Data Register	0.42	ns
t <sub>ISUD</sub>	Data Setup Time for the Input Data Register	0.47	ns
t <sub>IHD</sub>	Data Hold Time for the Input Data Register	0.00	ns
t <sub>ICLR2Q</sub>	Asynchronous Clear-to-Q of the Input Data Register	0.79	ns
t <sub>IPRE2Q</sub>	Asynchronous Preset-to-Q of the Input Data Register	0.79	ns
t <sub>IREMCLR</sub>	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
t <sub>IRECCLR</sub>	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
t <sub>IREMPRE</sub>	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
t <sub>IRECPRE</sub>	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t <sub>IWCLR</sub>	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t <sub>IWPRE</sub>	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
t <sub>ICKMPWH</sub>	Clock Minimum Pulse Width HIGH for the Input Data Register	0.31	ns
t <sub>ICKMPWL</sub>	Clock Minimum Pulse Width LOW for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



## 1.2 V DC Core Voltage

Table 2-80 • Input DDR Propagation Delays Commercial-Case Conditions:  $T_J = 70^{\circ}\text{C}$ , Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t <sub>DDRICLKQ1</sub>	Clock-to-Out Out_QR for Input DDR	0.76	ns
t <sub>DDRICLKQ2</sub>	Clock-to-Out Out_QF for Input DDR	0.94	ns
t <sub>DDRISUD1</sub>	Data Setup for Input DDR (negedge)	0.93	ns
t <sub>DDRISUD2</sub>	Data Setup for Input DDR (posedge)	0.84	ns
t <sub>DDRIHD1</sub>	Data Hold for Input DDR (negedge)	0.00	ns
t <sub>DDRIHD2</sub>	Data Hold for Input DDR (posedge)	0.00	ns
t <sub>DDRICLR2Q1</sub>	Asynchronous Clear-to-Out Out_QR for Input DDR	1.23	ns
t <sub>DDRICLR2Q2</sub>	Asynchronous Clear-to-Out Out_QF for Input DDR	1.42	ns
t <sub>DDRIREMCLR</sub>	Asynchronous Clear Removal Time for Input DDR	0.00	ns
t <sub>DDRIRECCLR</sub>	Asynchronous Clear Recovery Time for Input DDR	0.24	ns
t <sub>DDRIWCLR</sub>	Asynchronous Clear Minimum Pulse Width for Input DDR	0.19	ns
t <sub>DDRICKMPWH</sub>	Clock Minimum Pulse Width HIGH for Input DDR	0.31	ns
t <sub>DDRICKMPWL</sub>	Clock Minimum Pulse Width LOW for Input DDR	0.28	ns
F <sub>DDRIMAX</sub>	Maximum Frequency for Input DDR	160.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

## **VersaTile Characteristics**

## VersaTile Specifications as a Combinatorial Module

The IGLOO nano library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *IGLOO*, *ProASIC3*, *SmartFusion and Fusion Macro Library Guide for Software v10.1*.

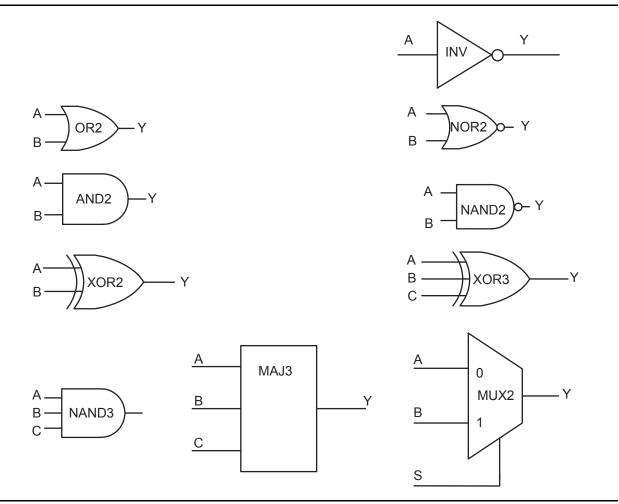


Figure 2-21 • Sample of Combinatorial Cells

## **Global Resource Characteristics**

## **AGLN125 Clock Tree Topology**

Clock delays are device-specific. Figure 2-25 is an example of a global tree used for clock routing. The global tree presented in Figure 2-25 is driven by a CCC located on the west side of the AGLN125 device. It is used to drive all D-flip-flops in the device.

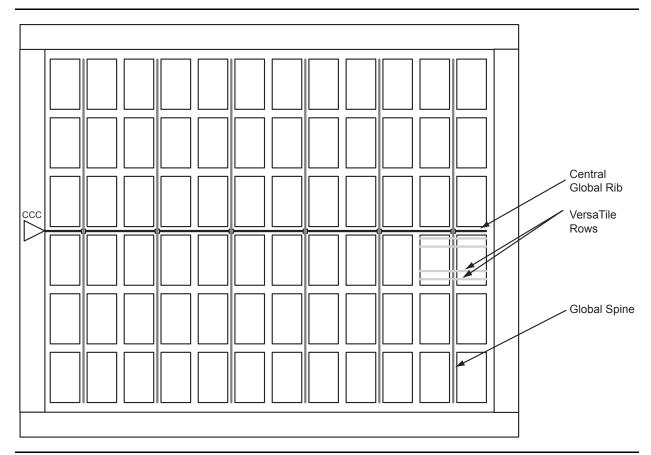


Figure 2-25 • Example of Global Tree Use in an AGLN125 Device for Clock Routing

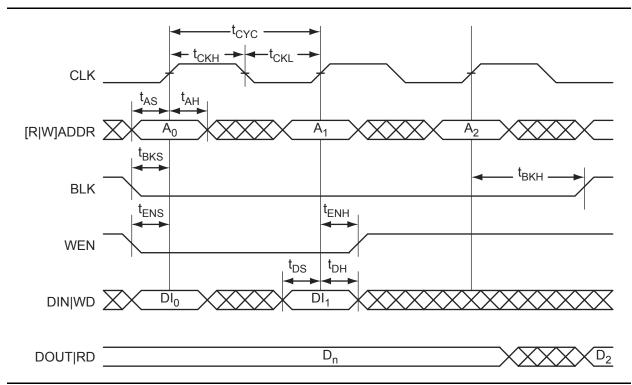


Figure 2-30 • RAM Write, Output Retained (WMODE = 0). Applicable to Both RAM4K9 and RAM512x18.

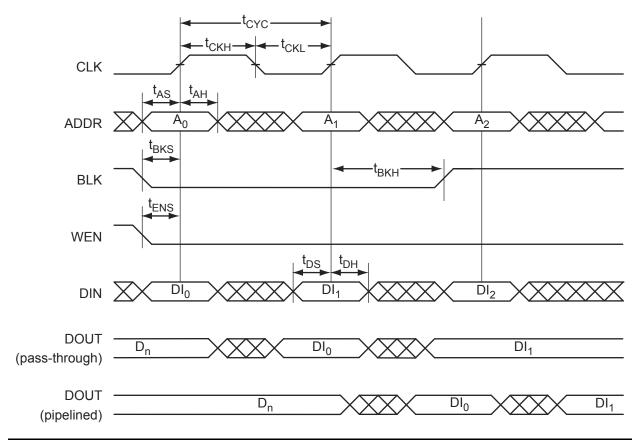


Figure 2-31 • RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 Only.



## 1.2 V DC Core Voltage

Table 2-104 • RAM4K9

Commercial-Case Conditions:  $T_J = 70$ °C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t <sub>AS</sub>	Address setup time	1.28	ns
t <sub>AH</sub>	Address hold time	0.25	ns
t <sub>ENS</sub>	REN, WEN setup time	1.25	ns
t <sub>ENH</sub>	REN, WEN hold time	0.25	ns
t <sub>BKS</sub>	BLK setup time	2.54	ns
t <sub>BKH</sub>	BLK hold time	0.25	ns
t <sub>DS</sub>	Input data (DIN) setup time	1.10	ns
t <sub>DH</sub>	Input data (DIN) hold time	0.55	ns
t <sub>CKQ1</sub>	Clock HIGH to new data valid on DOUT (output retained, WMODE = 0)	5.51	ns
	Clock HIGH to new data valid on DOUT (flow-through, WMODE = 1)	4.77	ns
t <sub>CKQ2</sub>	Clock HIGH to new data valid on DOUT (pipelined)	2.82	ns
t <sub>C2CWWL</sub> 1	Address collision clk-to-clk delay for reliable write after write on same address; applicable to closing edge	0.30	ns
t <sub>C2CRWH</sub> 1	Address collision clk-to-clk delay for reliable read access after write on same address; applicable to opening edge	0.89	ns
t <sub>C2CWRH</sub> 1	Address collision clk-to-clk delay for reliable write access after read on same address; applicable to opening edge	1.01	ns
t <sub>RSTBQ</sub>	RESET LOW to data out LOW on DOUT (flow-through)	3.21	ns
	RESET LOW to data out LOW on DO (pipelined)	3.21	ns
t <sub>REMRSTB</sub>	RESET removal	0.93	ns
t <sub>RECRSTB</sub>	RESET recovery	4.94	ns
t <sub>MPWRSTB</sub>	RESET minimum pulse width	1.18	ns
t <sub>CYC</sub>	Clock cycle time	10.90	ns
F <sub>MAX</sub>	Maximum frequency	92	MHz

### Notes:

<sup>1.</sup> For more information, refer to the application note AC374: Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based FPGAs and SoC FPGAs App Note.

<sup>2.</sup> For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.



IGLOO nano DC and Switching Characteristics

Table 2-105 • RAM512X18

## Commercial-Case Conditions: $T_J = 70^{\circ}C$ , Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t <sub>AS</sub>	Address setup time	1.28	ns
t <sub>AH</sub>	Address hold time	0.25	ns
t <sub>ENS</sub>	REN, WEN setup time	1.13	ns
t <sub>ENH</sub>	REN, WEN hold time	0.13	ns
t <sub>DS</sub>	Input data (WD) setup time	1.10	ns
t <sub>DH</sub>	Input data (WD) hold time	0.55	ns
t <sub>CKQ1</sub>	Clock High to new data valid on RD (output retained)	6.56	ns
t <sub>CKQ2</sub>	Clock High to new data valid on RD (pipelined)	2.67	ns
t <sub>C2CRWH</sub> 1	Address collision clk-to-clk delay for reliable read access after write on same address; applicable to opening edge	0.87	ns
t <sub>C2CWRH</sub> 1	Address collision clk-to-clk delay for reliable write access after read on same address; applicable to opening edge		ns
t <sub>RSTBQ</sub>	RESET LOW to data out LOW on RD (flow through)	3.21	ns
	RESET LOW to data out LOW on RD (pipelined)	3.21	ns
t <sub>REMRSTB</sub>	RESET removal	0.93	ns
t <sub>RECRSTB</sub>	RESET recovery	4.94	ns
t <sub>MPWRSTB</sub>	RESET minimum pulse width	1.18	ns
t <sub>CYC</sub>	Clock cycle time	10.90	ns
F <sub>MAX</sub>	Maximum frequency	92	MHz

### Notes:

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<sup>1.</sup> For more information, refer to the application note AC374: Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based FPGAs and SoC FPGAs App Note.

<sup>2.</sup> For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

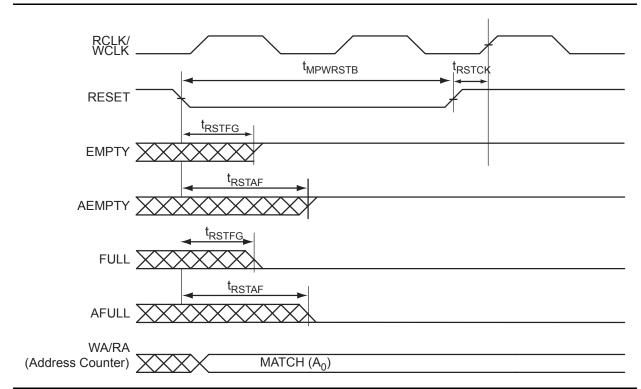


Figure 2-36 • FIFO Reset

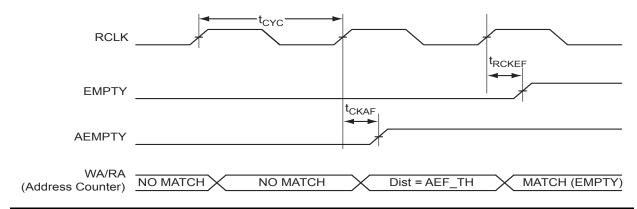


Figure 2-37 • FIFO EMPTY Flag and AEMPTY Flag Assertion



## 3 - Pin Descriptions

## **Supply Pins**

### GND Ground

Ground supply voltage to the core, I/O outputs, and I/O logic.

### GNDQ Ground (quiet)

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

### VCC Core Supply Voltage

Supply voltage to the FPGA core, nominally 1.5 V for IGLOO nano V5 devices, and 1.2 V or 1.5 V for IGLOO nano V2 devices. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

### VCCIBx I/O Supply Voltage

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on low power flash devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VCCI pins tied to GND.

### VMVx I/O Supply Voltage (quiet)

Quiet supply voltage to the input buffers of each I/O bank. *x* is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

### VCCPLA/B/C/D/E/F PLL Supply Voltage

Supply voltage to analog PLL, nominally 1.5 V or 1.2 V.

When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter in the *IGLOO nano FPGA Fabric User's Guide* for a complete board solution for the PLL analog power supply and ground.

There is one VCCPLF pin on IGLOO nano devices.

#### VCOMPLA/B/C/D/E/F PLL Ground

Ground to analog PLL power supplies. When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There is one VCOMPLF pin on IGLOO nano devices.

### VJTAG JTAG Supply Voltage

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG



	UC81				
	AGLN030Z				
Pin Number	Function				
A1	IO00RSB0				
A2	IO02RSB0				
A3	IO06RSB0				
A4	IO11RSB0				
A5	IO16RSB0				
A6	IO19RSB0				
A7	IO22RSB0				
A8	IO24RSB0				
A9	IO26RSB0				
B1	IO81RSB1				
B2	IO04RSB0				
В3	IO10RSB0				
B4	IO13RSB0				
B5	IO15RSB0				
В6	IO20RSB0				
B7	IO21RSB0				
B8	IO28RSB0				
B9	IO25RSB0				
C1	IO79RSB1				
C2	IO80RSB1				
C3	IO08RSB0				
C4	IO12RSB0				
C5	IO17RSB0				
C6	IO14RSB0				
C7	IO18RSB0				
C8	IO29RSB0				
C9	IO27RSB0				
D1	IO74RSB1				
D2	IO76RSB1				
D3	IO77RSB1				
D4	VCC				
D5	VCCIB0				
D6	GND				
D7	IO23RSB0				
D8	IO31RSB0				

UC81				
AGLN030Z				
Pin Number	Function			
D9	IO30RSB0			
E1	GEB0/IO71RSB1			
E2	GEA0/IO72RSB1			
E3	GEC0/IO73RSB1			
E4	VCCIB1			
E5	VCC			
E6	VCCIB0			
E7	GDC0/IO32RSB0			
E8	GDA0/IO33RSB0			
E9	GDB0/IO34RSB0			
F1	IO68RSB1			
F2	IO67RSB1			
F3	IO64RSB1			
F4	GND			
F5	VCCIB1			
F6	IO47RSB1			
F7	IO36RSB0			
F8	IO38RSB0			
F9	IO40RSB0			
G1	IO65RSB1			
G2	IO66RSB1			
G3	IO57RSB1			
G4	IO53RSB1			
G5	IO49RSB1			
G6	IO45RSB1			
G7	IO46RSB1			
G8	VJTAG			
G9	TRST			
H1	IO62RSB1			
H2	FF/IO60RSB1			
H3	IO58RSB1			
H4	IO54RSB1			
H5	IO48RSB1			
H6	IO43RSB1			
H7	IO42RSB1			

	UC81		
Pin Number	AGLN030Z Function		
H8	TDI		
H9	TDO		
J1	IO63RSB1		
J2	IO61RSB1		
J3	IO59RSB1		
J4	IO56RSB1		
J5	IO52RSB1		
J6	IO44RSB1		
J7	TCK		
J8	TMS		
J9	VPUMP		



Package Pin Assignments

	CS81
Pin Number	AGLN125Z Function
A1	GAA0/IO00RSB0
A2	GAA1/IO01RSB0
A3	GAC0/IO04RSB0
A4	IO13RSB0
A5	IO22RSB0
A6	IO32RSB0
A7	GBB0/IO37RSB0
A8	GBA1/IO40RSB0
A9	GBA2/IO41RSB0
B1	GAA2/IO132RSB1
B2	GAB0/IO02RSB0
В3	GAC1/IO05RSB0
B4	IO11RSB0
B5	IO25RSB0
В6	GBC0/IO35RSB0
В7	GBB1/IO38RSB0
B8	IO42RSB0
В9	GBB2/IO43RSB0
C1	GAB2/IO130RSB1
C2	IO131RSB1
C3	GND
C4	IO15RSB0
C5	IO28RSB0
C6	GND
C7	GBA0/IO39RSB0
C8	GBC2/IO45RSB0
C9	IO47RSB0
D1	GAC2/IO128RSB1
D2	IO129RSB1
D3	GFA2/IO117RSB1
D4	VCC
D5	VCCIB0
D6	GND
D7	GCC2/IO59RSB0
D8	GCC1/IO51RSB0
D9	GCC0/IO52RSB0

CS81			
Pin Number	AGLN125Z Function		
E1	GFB0/IO120RSB1		
E2	GFB1/IO121RSB1		
E3	GFA1/IO118RSB1		
E4	VCCIB1		
E5	VCC		
E6	VCCIB0		
E7	GCA0/IO56RSB0		
E8	GCA1/IO55RSB0		
E9	GCB2/IO58RSB0		
F1*	VCCPLF		
F2*	VCOMPLF		
F3	GND		
F4	GND		
F5	VCCIB1		
F6	GND		
F7	GDA1/IO65RSB0		
F8	GDC1/IO61RSB0		
F9	GDC0/IO62RSB0		
G1	GEA0/IO104RSB1		
G2	GEC0/IO108RSB1		
G3	GEB1/IO107RSB1		
G4	IO96RSB1		
G5	IO92RSB1		
G6	IO72RSB1		
G7	GDB2/IO68RSB1		
G8	VJTAG		
G9	TRST		
H1	GEA1/IO105RSB1		
H2	FF/GEB2/IO102RSB1		
НЗ	IO99RSB1		
H4	IO94RSB1		
H5	IO91RSB1		
H6	IO81RSB1		
H7	GDA2/IO67RSB1		
H8	TDI		
H9	TDO		

CS81			
Pin Number	AGLN125Z Function		
J1	GEA2/IO103RSB1		
J2	GEC2/IO101RSB1		
J3	IO97RSB1		
J4	IO93RSB1		
J5	IO90RSB1		
J6	IO78RSB1		
J7	TCK		
J8	TMS		
J9	VPUMP		

Note: \* Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN125Z-CS81.

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	CS81
Pin Number	AGLN250 Function
A1	GAA0/IO00RSB0
A2	GAA1/IO01RSB0
A3	GAC0/IO04RSB0
A4	IO07RSB0
A5	IO09RSB0
A6	IO12RSB0
A7	GBB0/IO16RSB0
A8	GBA1/IO19RSB0
A9	GBA2/IO20RSB1
B1	GAA2/IO67RSB3
B2	GAB0/IO02RSB0
В3	GAC1/IO05RSB0
B4	IO06RSB0
B5	IO10RSB0
В6	GBC0/IO14RSB0
В7	GBB1/IO17RSB0
B8	IO21RSB1
В9	GBB2/IO22RSB1
C1	GAB2/IO65RSB3
C2	IO66RSB3
C3	GND
C4	IO08RSB0
C5	IO11RSB0
C6	GND
C7	GBA0/IO18RSB0
C8	GBC2/IO23RSB1
C9	IO24RSB1
D1	GAC2/IO63RSB3
D2	IO64RSB3
D3	GFA2/IO56RSB3
D4	VCC
D5	VCCIB0
D6	GND
D7	IO30RSB1
D8	GCC1/IO25RSB1
D9	GCC0/IO26RSB1

	CS81
Pin Number	AGLN250 Function
E1	GFB0/IO59RSB3
E2	GFB1/IO60RSB3
E3	GFA1/IO58RSB3
E4	VCCIB3
E5	VCC
E6	VCCIB1
E7	GCA0/IO28RSB1
E8	GCA1/IO27RSB1
E9	GCB2/IO29RSB1
F1	VCCPLF
F2	VCOMPLF
F3	GND
F4	GND
F5	VCCIB2
F6	GND
F7	GDA1/IO33RSB1
F8	GDC1/IO31RSB1
F9	GDC0/IO32RSB1
G1	GEA0/IO51RSB3
G2	GEC1/IO54RSB3
G3	GEC0/IO53RSB3
G4	IO45RSB2
G5	IO42RSB2
G6	IO37RSB2
G7	GDB2/IO35RSB2
G8	VJTAG
G9	TRST
H1	GEA1/IO52RSB3
H2	FF/GEB2/IO49RSB2
H3	IO47RSB2
H4	IO44RSB2
H5	IO41RSB2
H6	IO39RSB2
H7	GDA2/IO34RSB2
H8	TDI
H9	TDO

CS81	
Pin Number	AGLN250 Function
J1	GEA2/IO50RSB2
J2	GEC2/IO48RSB2
J3	IO46RSB2
J4	IO43RSB2
J5	IO40RSB2
J6	IO38RSB2
J7	TCK
J8	TMS
J9	VPUMP
J9	VPUMP

Note: \* Pin numbers F1 and F2 must be connected to ground because a PLL is not supported for AGLN250-CS81.



## Package Pin Assignments

Pin Number	AGLN010 Function
1	GEC0/IO37RSB1
2	IO36RSB1
3	GEA0/IO34RSB1
4	IO22RSB1
5	GND
6	VCCIB1
7	IO24RSB1
8	IO33RSB1
9	IO26RSB1
10	IO32RSB1
11	IO27RSB1
12	IO29RSB1
13	IO30RSB1
14	FF/IO31RSB1
15	IO28RSB1
16	IO25RSB1
17	IO23RSB1
18	VCC
19	VCCIB1
20	IO17RSB1
21	IO14RSB1
22	TCK
23	TDI
24	TMS
25	VPUMP
26	TDO
27	TRST
28	VJTAG
29	IO11RSB0
30	IO10RSB0
31	IO09RSB0
32	IO08RSB0
33	VCCIB0
34	GND
35	VCC

QN48	
Pin Number	AGLN010 Function
36	IO07RSB0
37	IO06RSB0
38	GDA0/IO05RSB0
39	IO03RSB0
40	GDC0/IO01RSB0
41	IO12RSB1
42	IO13RSB1
43	IO15RSB1
44	IO16RSB1
45	IO18RSB1
46	IO19RSB1
47	IO20RSB1
48	IO21RSB1

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	QN68
	AGLN015
Pin Number	Function
1	IO60RSB2
2	IO54RSB2
3	IO52RSB2
4	IO50RSB2
5	IO49RSB2
6	GEC0/IO48RSB2
7	GEA0/IO47RSB2
8	VCC
9	GND
10	VCCIB2
11	IO46RSB2
12	IO45RSB2
13	IO44RSB2
14	IO43RSB2
15	IO42RSB2
16	IO41RSB2
17	IO40RSB2
18	FF/IO39RSB1
19	IO37RSB1
20	IO35RSB1
21	IO33RSB1
22	IO31RSB1
23	IO30RSB1
24	VCC
25	GND
26	VCCIB1
27	IO27RSB1
28	IO25RSB1
29	IO23RSB1
30	IO21RSB1
31	IO19RSB1
32	TCK
33	TDI
34	TMS
35	VPUMP

	QN68
•	
Pin Number	AGLN015 Function
36	TDO
37	TRST
38	VJTAG
39	IO17RSB0
40	IO16RSB0
41	GDA0/IO15RSB0
42	GDC0/IO14RSB0
43	IO13RSB0
44	VCCIB0
45	GND
46	VCC
47	IO12RSB0
48	IO11RSB0
49	IO09RSB0
50	IO05RSB0
51	IO00RSB0
52	IO07RSB0
53	IO03RSB0
54	IO18RSB1
55	IO20RSB1
56	IO22RSB1
57	IO24RSB1
58	IO28RSB1
59	NC
60	GND
61	NC
62	IO32RSB1
63	IO34RSB1
64	IO36RSB1
65	IO61RSB2
66	IO58RSB2
67	IO56RSB2
68	IO63RSB2

## Datasheet Information

Revision	Changes	Page
Revision 12 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34663).	I, 1-2
	Notes indicating that AGLN015 is not recommended for new designs have been added (SAR 35759).	III, IV
	Notes indicating that nano-Z devices are not recommended for new designs have been added. The "Devices Not Recommended For New Designs" section is new (SAR 36759).	
Revision 12 (continued)	The Y security option and Licensed DPA Logo were added to the "IGLOO nano Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34722).	IV
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry enables rapid, single-voltage (3.3 V) programming of IGLOO nano devices via an IEEE 1532 JTAG interface" (SAR 34683).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 34694).	1-9
	The reference to guidelines for global spines and VersaTile rows, given in the "Global Clock Contribution—P <sub>CLOCK</sub> " section, was corrected to the "Spine Architecture" section of the Global Resources chapter in the <i>IGLOO nano FPGA Fabric User's Guide</i> (SAR 34732).	2-12
	Figure 2-4 has been modified for DIN waveform; the Rise and Fall time label has been changed to tDIN (37106).	2-16
	The AC Loading figures in the "Single-Ended I/O Characteristics" section were updated to match tables in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section (SAR 34885).	2-26, 2-20
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section, "3.3 V LVCMOS Wide Range" section and "1.2 V LVCMOS Wide Range" section tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is $\pm 100~\mu A$ . The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 34765).	2-20, 2-29, 2-40
	Added values for minimum pulse width and removed the FRMAX row from Table 2-88 through Table 2-99 in the "Global Tree Timing Characteristics" section. Use the software to determine the FRMAX for the device you are using (SAR 36953).	2-64 to 2-69
	Table 2-100 • IGLOO nano CCC/PLL Specification and Table 2-101 • IGLOO nano CCC/PLL Specification were updated. A note was added indicating that when the CCC/PLL core is generated by Mircosemi core generator software, not all delay values of the specified delay increments are available (SAR 34817).	2-70 and 2-71
	The port names in the SRAM "Timing Waveforms", SRAM "Timing Characteristics" tables, Figure 2-36 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SAR 35754).	2-74, 2-77, 2-85
	Reference was made to a new application note, Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs, which covers these cases in detail (SAR 34865).	
	The "Pin Descriptions" chapter has been added (SAR 34770).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 34770).	4-1

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## Datasheet Information

Revision / Version	Changes	Page
Revision 2 (Dec 2008) Product Brief Advance v0.4	The second table note in "IGLOO nano Devices" table was revised to state, "AGLN060, AGLN125, and AGLN250 in the CS81 package do not support PLLs. AGLN030 and smaller devices do not support this feature."	II
	The I/Os per package for CS81 were revised to 60 for AGLN060, AGLN125, and AGLN250 in the "I/Os Per Package"table.	II
Packaging Advance v0.3	The "UC36" pin table is new.	4-2
Revision 1 (Nov 2008)	The "Advanced I/Os" section was updated to include wide power supply voltage	I
Product Brief Advance v0.3	support for 1.14 V to 1.575 V.	
	The AGLN030 device was added to product tables and replaces AGL030 entries that were formerly in the tables.	VI
	The "I/Os Per Package"table was updated for the CS81 package to change the number of I/Os for AGLN060, AGLN125, and AGLN250 from 66 to 64.	II
	The "Wide Range I/O Support" section is new.	1-8
	The table notes and references were revised in Table 2-2 • Recommended Operating Conditions <sup>1</sup> . VMV was included with VCCI and a table note was added stating, "VMV pins must be connected to the corresponding VCCI pins. See <i>Pin Descriptions</i> for further information." Please review carefully.	2-2
	VJTAG was added to the list in the table note for Table 2-9 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Flash*Freeze Mode*. Values were added for AGLN010, AGLN015, and AGLN030 for 1.5 V.	2-7
	VCCI was removed from the list in the table note for Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO nano Sleep Mode*.	2-8
	Values for I <sub>CCA</sub> current were updated for AGLN010, AGLN015, and AGLN030 in Table 2-12 • Quiescent Supply Current (IDD), No IGLOO nano Flash*Freeze Mode <sup>1</sup> .	2-8
	Values for PAC1 and PAC2 were added to Table 2-15 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices and Table 2-17 • Different Components Contributing to Dynamic Power Consumption in IGLOO nano Devices.	2-10, 2-11
	Table notes regarding wide range support were added to Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels.	2-19
	1.2 V LVCMOS wide range values were added to Table 2-22 • Summary of Maximum and Minimum DC Input Levels and Table 2-23 • Summary of AC Measuring Points.	2-19, 2-20
	The following table note was added to Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings and Table 2-26 • Summary of I/O Timing Characteristics—Software Default Settings: "All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range, as specified in the JESD8-B specification."	2-21
	3.3 V LVCMOS Wide Range and 1.2 V Wide Range were added to Table 2-28 • I/O Output Buffer Maximum Resistances <sup>1</sup> and Table 2-30 • I/O Short Currents IOSH/IOSL.	2-23, 2-24

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Datasheet Information

## **Datasheet Categories**

### **Categories**

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "IGLOO nano Device Status" table on page III, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

### **Product Brief**

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

#### Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

### **Preliminary**

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

### Unmarked (production)

This version contains information that is considered to be final.

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